

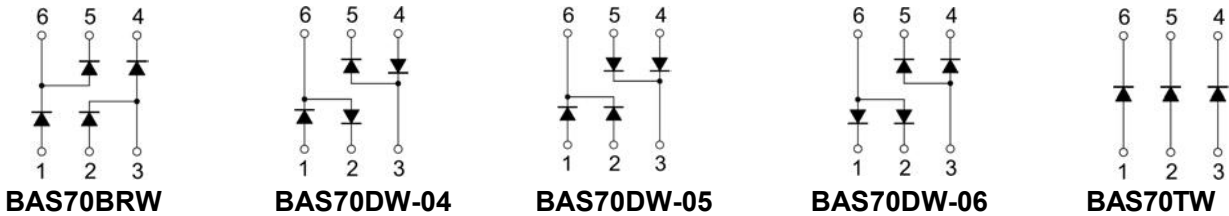
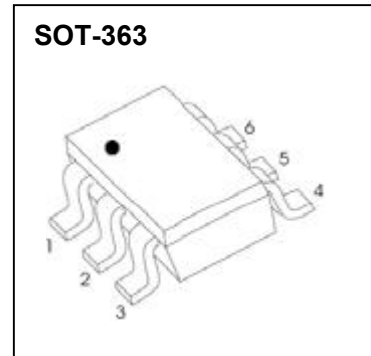


Plastic-Encapsulate Diodes

SCHOTTKY BARRIER DIODE ARRAYS

FEATURES

- Low Forward Voltage Drop
- Fast Switching
- Small Surface Mount Package
- PN Junction Guard Ring for Transient and ESD Protection
- Available in Lead Free Version



MARKING:

BAS70BRW	BAS70DW-04	BAS70DW-05	BA S70DW-06	BA S70TW

Solid dot = Green molding compound device, if none, the normal device.

Solid dot = Pin1 indicate.

MAXIMUM RATINGS ($T_a=25^\circ\text{C}$ unless otherwise noted)

Symbol	Parameter	Value	Unit
V_{RRM}	Repetitive Peak Reverse Voltage	70	V
V_{RWM}	Peak Working Reverse Voltage		
V_R	DC Blocking Voltage		
$V_{R(RMS)}$	RMS Reverse Voltage	49	V
I_O	Forward Continuous Current	70	mA
I_{FSM}	Non-repetitive Peak Forward Surge Current @ $t=8.3\text{ms}$	100	mA
P_D	Power Dissipation	200	mW
$R_{\theta JA}$	Thermal Resistance From Junction To Ambient	500	$^\circ\text{C}/\text{W}$
T_j	Operating Junction Temperature Range	-40 ~ +125	$^\circ\text{C}$
T_{stg}	Storage Temperature Range	-55 ~ +150	$^\circ\text{C}$



ELECTRICAL CHARACTERISTICS

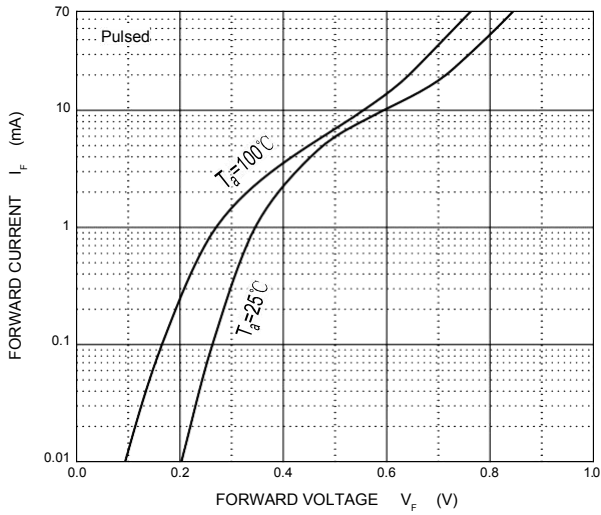
$T_a=25\text{ }^\circ\text{C}$ unless otherwise specified

Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Reverse voltage	$V_{(BR)}$	$I_R=10\mu\text{A}$	70			V
Reverse current	I_R	$V_R=50\text{V}$			0.1	μA
Forward voltage	V_F	$I_F=1\text{mA}$			0.41	V
		$I_F=15\text{mA}$			1	
Total capacitance	C_{tot}	$V_R=0\text{V}, f=1\text{MHz}$			2	pF
Reverse recovery time	t_{rr}	$I_F=I_R=10\text{mA}$ to $I_R=1\text{mA}, I_{tr}=0.1\times I_R, R_L=100\Omega$			5	ns

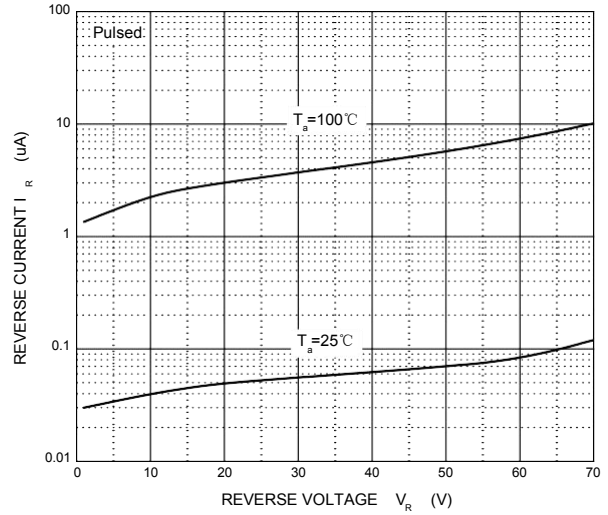


Typical Characteristics

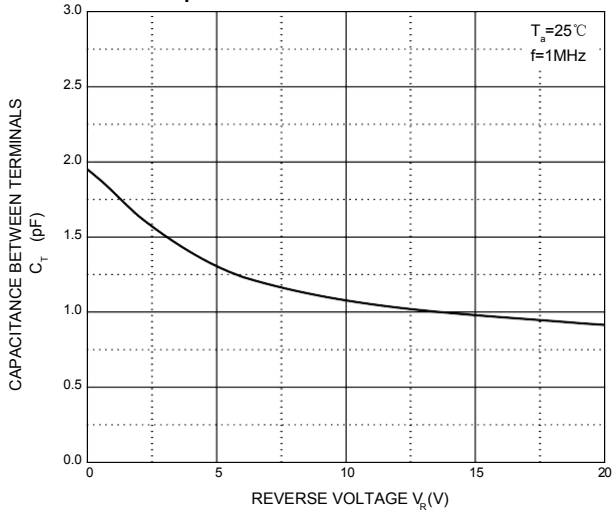
Forward Characteristics



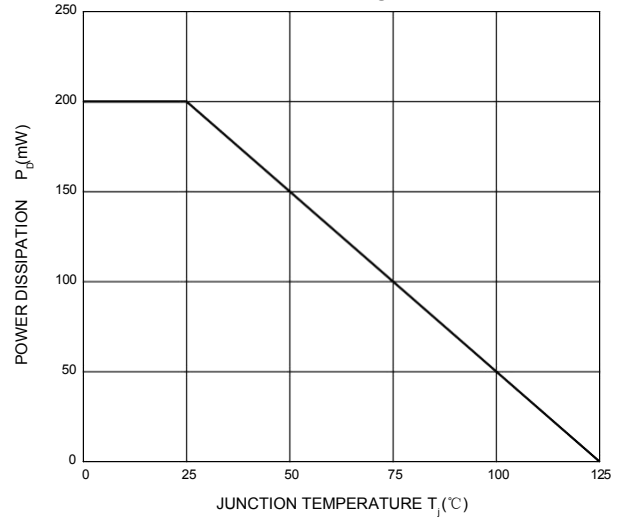
Reverse Characteristics



Capacitance Characteristics Per Diode

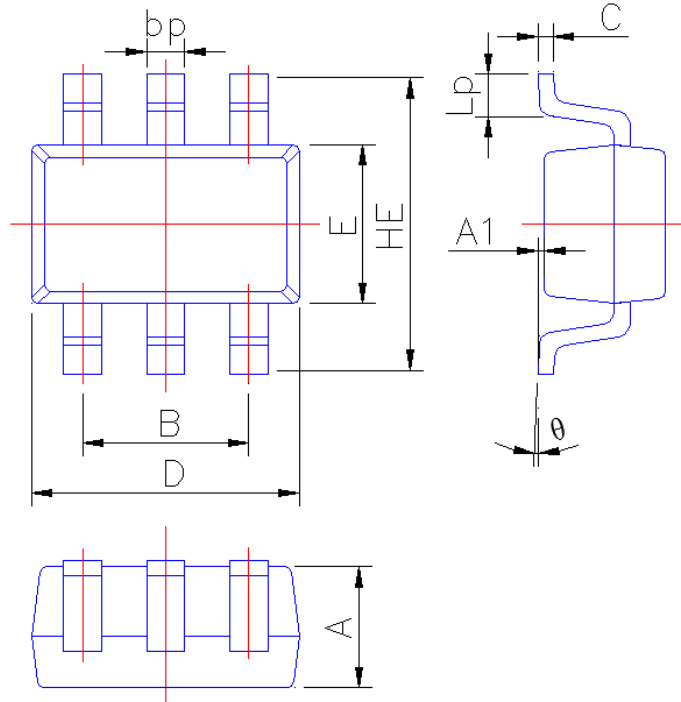


Power Derating Curve





SOT-363 Package Outline Dimensions



Symbol	Dimension in Millimeters	
	Min	Max
A	0.90	1.00
A1	0.010	0.100
B	1.20	1.40
bp	0.25	0.45
C	0.09	0.15
D	2.00	2.20
E	1.15	1.35
HE	2.15	2.55
Lp	0.25	0.46
theta	0°	6°